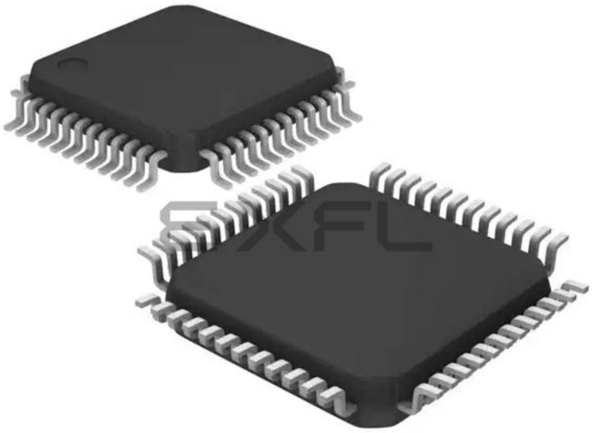
Renesas Electronics America Inc - R5F10RGCAFB#X0 Datasheet



Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	33
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rgcafb-x0

1.3.3 48-pin products

- 48-pin plastic LQFP (fine pitch) (7 × 7)

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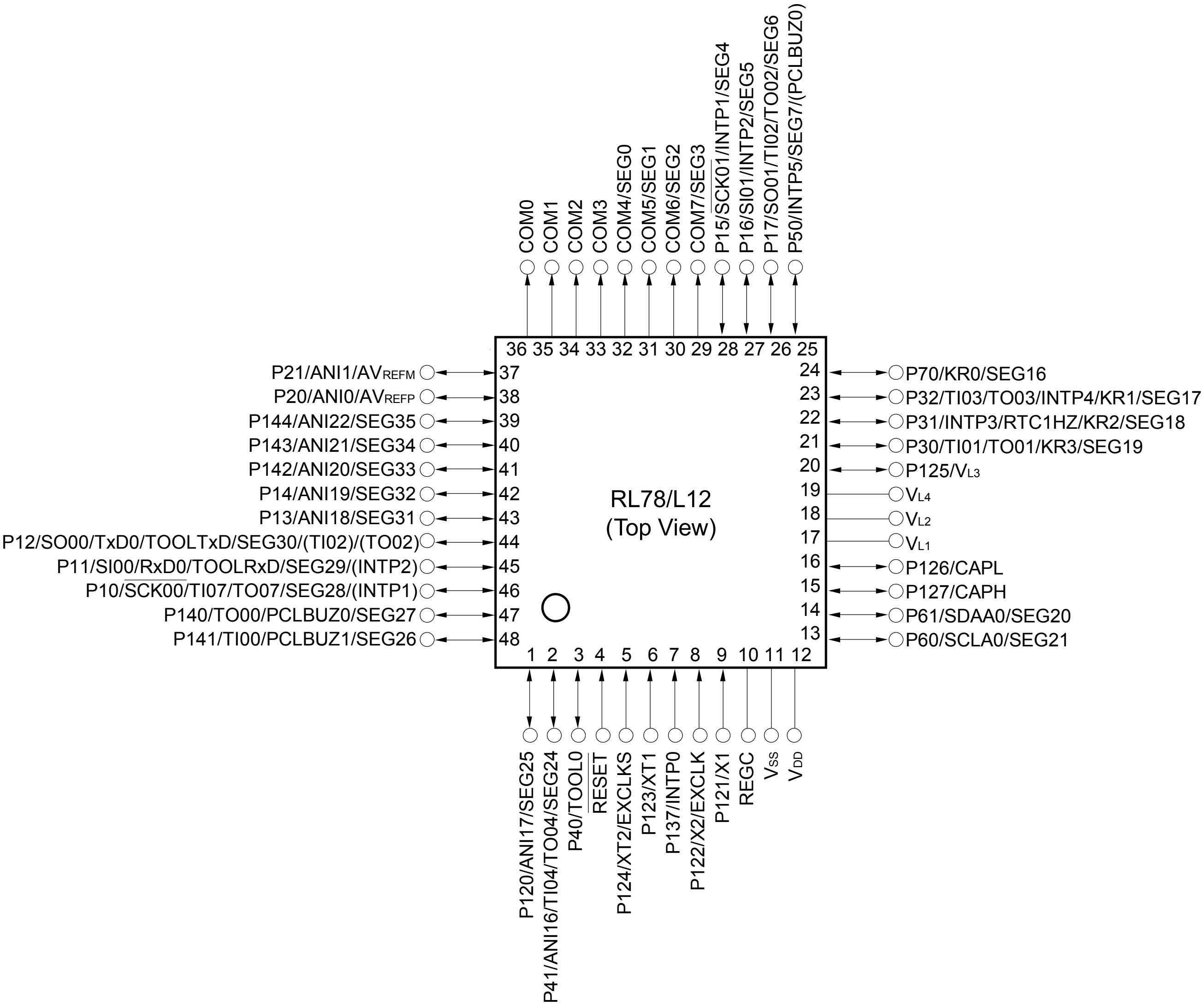

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

- 64-pin plastic LQFP (fine pitch) (10 × 10)
- 64-pin plastic LQFP (12 × 12)

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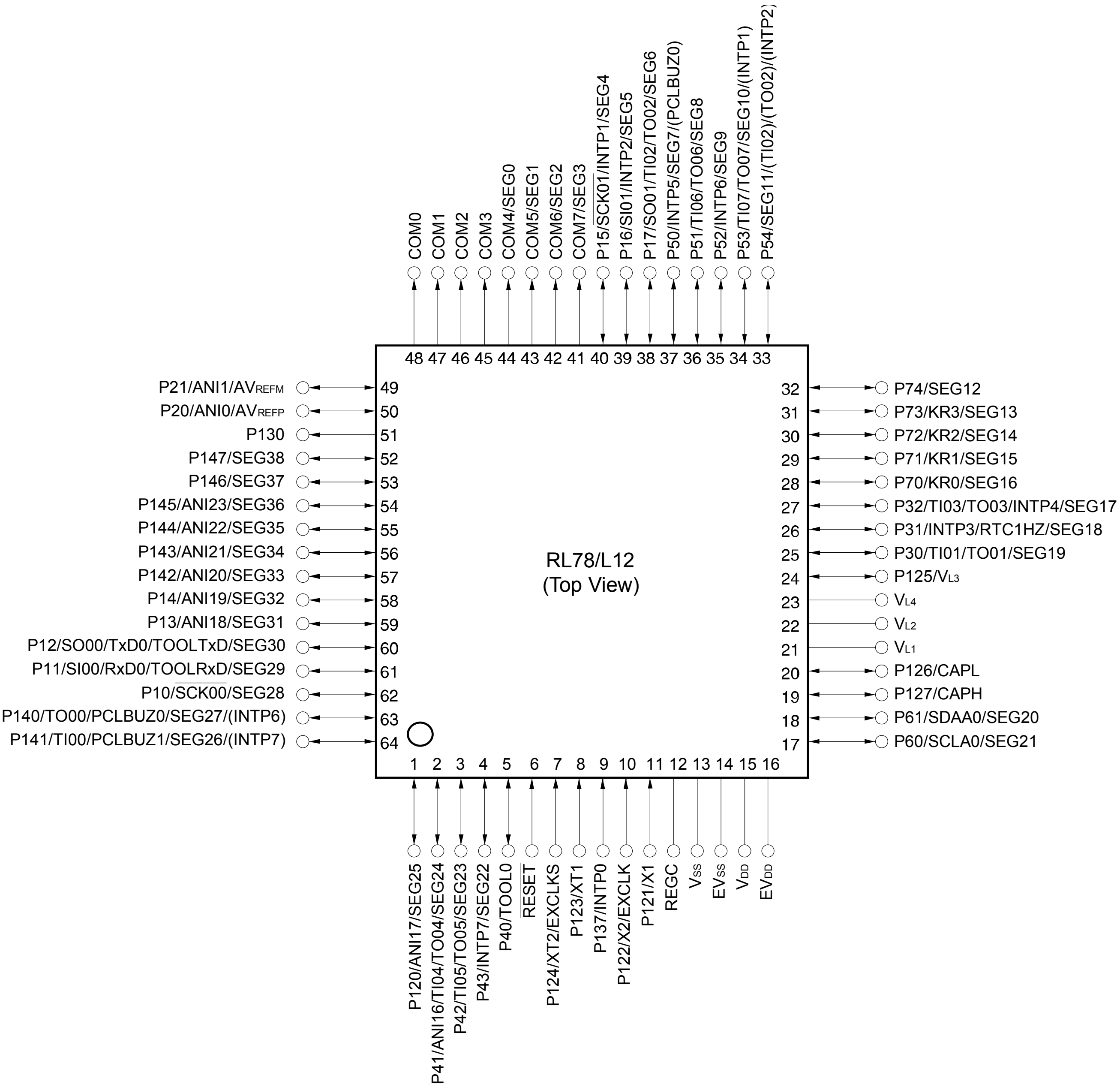


Cautions 1. Make EV$_{SS}$ pin the same potential as V$_{SS}$ pin.

2. Make V$_{DD}$ pin the same potential as EV$_{DD}$ pin.

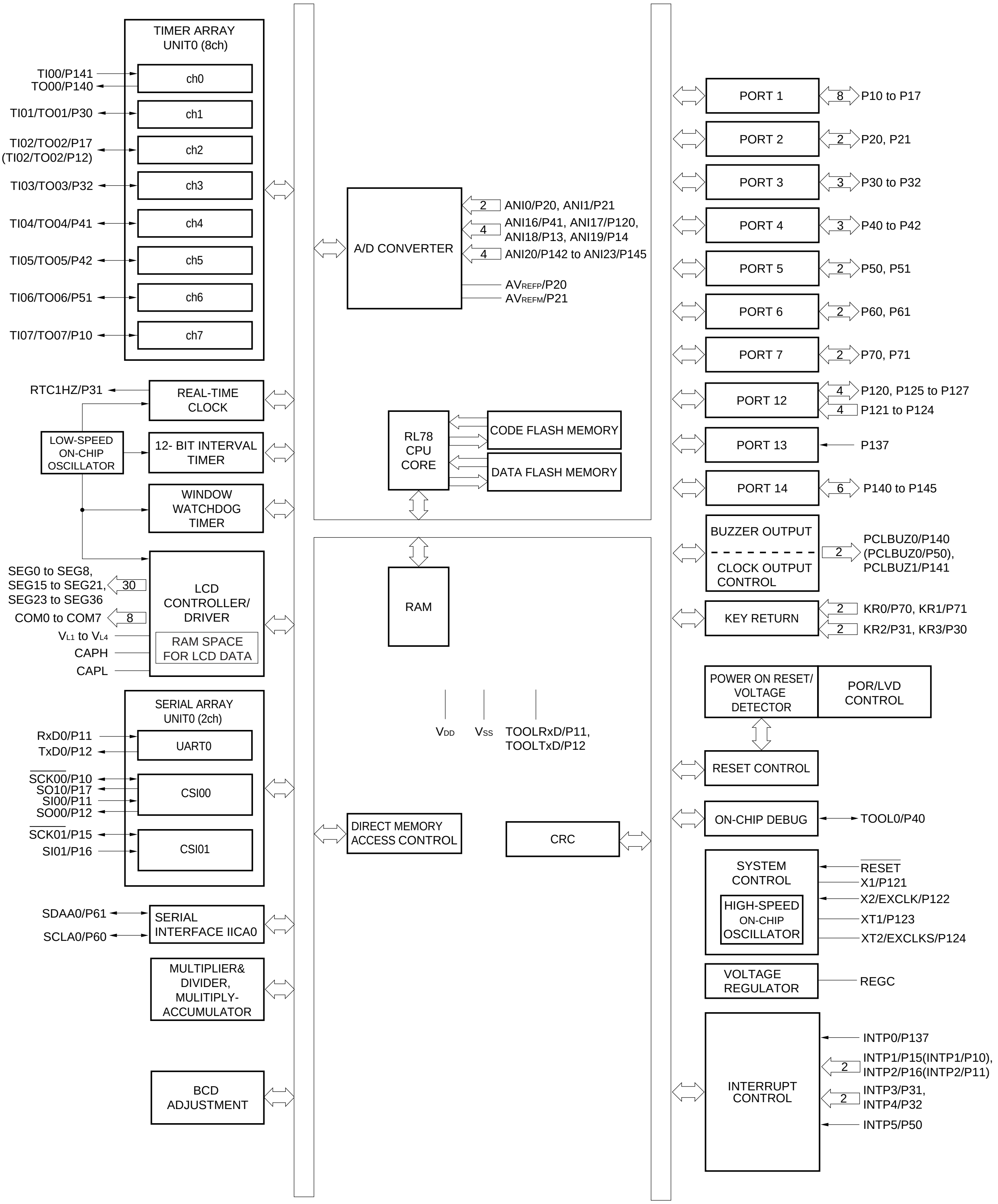
3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification.**

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V$_{DD}$ and EV$_{DD}$ pins and connect the V$_{SS}$ and EV$_{SS}$ pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.5.4 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

2. ELECTRICAL SPECIFICATIONS (A, G: T_A = -40 to +85°C)

This chapter describes the electrical specifications for the products "A: Consumer applications (T_A = -40 to +85°C)" and "G: Industrial applications (with T_A = -40 to +85°C)".

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. With products not provided with an EV_{DD}, or EV_{SS} pin, replace EV_{DD} with V_{DD}, or replace EV_{SS} with V_{SS}.

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –10 mA	EV_{DD}–1.5			V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	EV_{DD}–0.7			V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	EV_{DD}–0.6			V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	EV_{DD}–0.5			V
			1.6 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.0 mA	EV_{DD}–0.5			V
	V_{OH2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = –100 μA	V_{DD}–0.5			V
Output voltage, low	V_{OL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution P10, P12, P15, P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.4 AC Characteristics

2.4.1 Basic operation

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LV (low voltage main) mode	1.6 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
		Subsystem clock (f_{SUB}) operation		1.8 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LV (low voltage main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V_{DD} < 1.8 V			1.0		4.0	MHz
	f_{EXS}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
		1.6 V ≤ V_{DD} < 1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				$1/f_{MCK}+10$			ns
TO00 to TO07 output frequency	f_{TO}	HS (high-speed main) mode	4.0 V ≤ EV_{DD} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV_{DD} < 4.0 V				8	MHz
			2.4 V ≤ EV_{DD} < 2.7 V				4	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD} ≤ 5.5 V				4	MHz
		LV (low voltage main) mode	1.6 V ≤ EV_{DD} ≤ 5.5 V				2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	4.0 V ≤ EV_{DD} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV_{DD} < 4.0 V				8	MHz
			2.4 V ≤ EV_{DD} < 2.7 V				4	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD} ≤ 5.5 V				4	MHz
		LV (low-voltage main) mode	1.8 V ≤ EV_{DD} ≤ 5.5 V				4	MHz
			1.6 V ≤ EV_{DD} < 1.8 V				2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0	1.6 V ≤ V_{DD} ≤ 5.5 V		1			μs
		INTP1 to INTP7	1.6 V ≤ EV_{DD} ≤ 5.5 V		1			μs
Key interrupt input low-level width	t_{KR}	KR0 to KR3	1.8 V ≤ EV_{DD} ≤ 5.5 V		250			ns
			1.6 V ≤ EV_{DD} < 1.8 V		1			μs
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),
g: PIM and POM numbers (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 5]	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V	16 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 2.4 V				6/f_{MCK}		6/f_{MCK}		ns
		1.6 V ≤ EV_{DD} < 1.8 V						6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY2}/2 − 7		t_{KCY2}/2 − 7		t_{KCY2}/2 − 7		ns
		2.7 V ≤ EV_{DD} < 4.0 V		t_{KCY2}/2 − 8		t_{KCY2}/2 − 8		t_{KCY2}/2 − 8		ns
		2.4 V ≤ EV_{DD} < 2.7 V		t_{KCY2}/2 − 18		t_{KCY2}/2 − 18		t_{KCY2}/2 − 18		ns
		1.8 V ≤ EV_{DD} < 2.4 V				t_{KCY2}/2 − 18		t_{KCY2}/2 − 18		ns
		1.6 V ≤ EV_{DD} < 1.8 V						t_{KCY2}/2 − 66		ns
SIp setup time (to SCKp↑)[Note 1]	t_{SIK2}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 2.7 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑)[Note 2]	t_{KSI2}	2.4 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 250		ns

(**Notes**, **Caution,** and **Remarks** are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +85°C, 1.8 V ≤ $EV_{DD} = V_{DD} \le$ 5.5 V, $V_{SS} = EV_{SS}$ = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	$4.0 \text{ V} \le EV_{DD} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 1.4 \text{ k}\Omega$	19		19		19		ns
		$2.7 \text{ V} \le EV_{DD} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$	19		19		19		ns
		$2.4 \text{ V} \le EV_{DD} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$	19		19		19		ns
		$1.8 \text{ V} \le EV_{DD} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$ Note 3, $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$			19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	$4.0 \text{ V} \le EV_{DD} \le 5.5 \text{ V}$, $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 1.4 \text{ k}\Omega$		25		25		25	ns
		$2.7 \text{ V} \le EV_{DD} < 4.0 \text{ V}$, $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$		25		25		25	ns
		$2.4 \text{ V} \le EV_{DD} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$, $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$		25		25		25	ns
		$1.8 \text{ V} \le EV_{DD} < 3.3 \text{ V}$, $1.6 \text{ V} \le V_b \le 2.0 \text{ V}$ Note 3, $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$				25		25	ns

Notes
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
3. Use it with $EV_{DD} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (32-pin to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2.5.2 Serial interface IICA

(1) I^2C standard mode

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MIN.	MAX.	MIN.	
SCLA0 clock frequency	f_{SCL}	Standard mode: f_{CLK} ≥ 1 MHz	2.7 V ≤ EV_{DD} ≤ 5.5 V	0	100	0	100	0	100	kHz
			2.4 V ≤ EV_{DD} ≤ 5.5 V	0	100	0	100	0	100	
			1.8 V ≤ EV_{DD} ≤ 5.5 V			0	100	0	100	
			1.6 V ≤ EV_{DD} ≤ 5.5 V					0	100	
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.7		4.7		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.7		
Hold time [Note 1]	$t_{HD:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.0		4.0		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.0		
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.7		4.7		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.7		
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.0		4.0		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.0		
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		250		250		250		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		250		250		250		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				250		250		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						250		
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	
		1.8 V ≤ EV_{DD} ≤ 5.5 V				0	3.45	0	3.45	
		1.6 V ≤ EV_{DD} ≤ 5.5 V						0	3.45	
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.0		4.0		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.0		
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		
		1.8 V ≤ EV_{DD} ≤ 5.5 V				4.7		4.7		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						4.7		

(**Notes** and **Remark** are listed on the next page.)

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the $\overline{ACK}$ (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0, ANI1, ANI16 to ANI23, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	t_{CONV}	10-bit resolution	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	V_{AIN}	ANI0, ANI1		0		V_{DD}	V
		ANI16 to ANI23		0		EV_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} Note 4			V

Notes **1.** Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

<R>

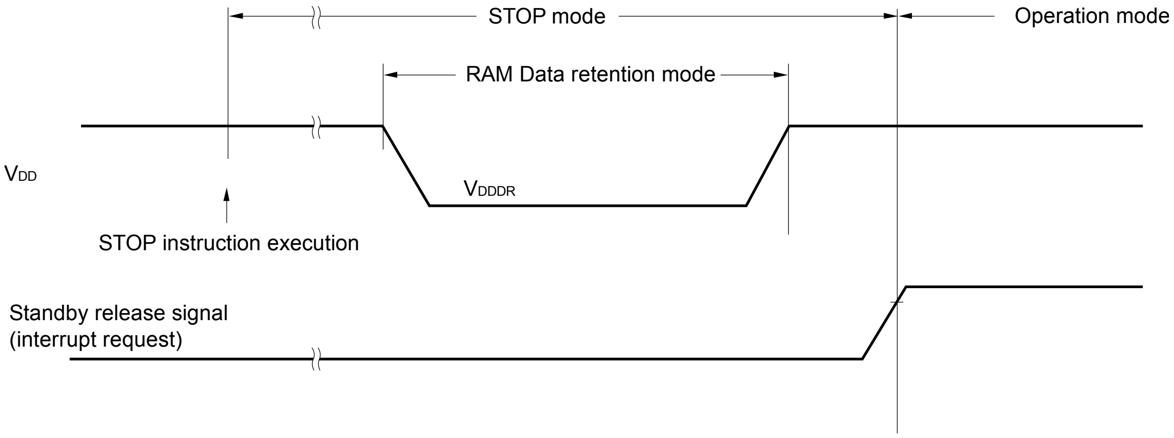
2.8 RAM Data Retention Characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46^{Note}		5.5	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

<R>



2.9 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	System clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		24	MHz
<R>	Number of code flash rewrites Note 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
<R>	Number of data flash rewrites Note 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
<R>			Retained for 5 years T_A = 85°C	100,000			
<R>			Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.
The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During flash memory programming	115,200		1,000,000	bps

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) **(3/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV_{DD}		EV_{DD}	V
	V_{IH2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV_{DD} ≤ 5.5 V	2.2		EV_{DD}	V
			TTL input buffer 3.3 V ≤ EV_{DD} < 4.0 V	2.0		EV_{DD}	V
			TTL input buffer 2.4 V ≤ EV_{DD} < 3.3 V	1.50		EV_{DD}	V
	V_{IH3}	P20, P21		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7EV_{DD}		EV_{DD}	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{RESET}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV_{DD}	V
	V_{IL2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV_{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV_{DD} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20, P21		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3EV_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{RESET}$		0		0.2V_{DD}	V

Caution The maximum value of V_{IH} of pins P10, P12, P15, and P17 is EV_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) **(2/3)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.44	2.3	mA
					V_{DD} = 3.0 V		0.44	2.3	mA
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.40	1.7	mA
					V_{DD} = 3.0 V		0.40	1.7	mA
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	1.9	mA
					Resonator connection		0.45	2.0	mA
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	1.9	mA
					Resonator connection		0.45	2.0	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = –40°C	Square wave input		0.31	0.57	μA
					Resonator connection		0.50	0.76	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.37	0.57	μA
					Resonator connection		0.56	0.76	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.46	1.17	μA
					Resonator connection		0.65	1.36	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.57	1.97	μA
					Resonator connection		0.76	2.16	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		0.85	3.37	μA
					Resonator connection		1.04	3.56	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +105°C	Square wave input		3.04	15.37	μA
					Resonator connection		3.23	15.56	μA
	I_{DD3} Note 6	STOP mode Note 8	T_A = –40°C				0.17	0.50	μA
			T_A = +25°C				0.23	0.50	μA
			T_A = +50°C				0.32	1.10	μA
			T_A = +70°C				0.43	1.90	μA
			T_A = +85°C				0.71	3.30	μA
			T_A = +105°C				2.90	15.30	μA

(**Notes** and **Remarks** are listed on the next page.)

(T_A = –40 to +105°C, 2.4 V ≤ $EV_{DD} = V_{DD}$ ≤ 5.5 V, $V_{SS} = EV_{SS}$ = 0 V) **(3/3)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3	f_{MAIN} is stopped			0.08		μA
12-bit interval timer current	I_{IT} Notes 1, 2, 4				0.08		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.24		μA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, $AV_{REFP} = V_{DD}$ = 5.0 V		1.3	1.7	mA
			Low voltage mode, $AV_{REFP} = V_{DD}$ = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
LVD operating current	I_{LVD} Notes 1, 7				0.08		μA
Self-programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
LCD operating current	I_{LCD1} Notes 11, 12	External resistance division method	$V_{DD} = EV_{DD}$ = 5.0 V V_{L4} = 5.0 V		0.04	0.20	μA
	I_{LCD2} Note 11	Internal voltage boosting method	$V_{DD} = EV_{DD}$ = 5.0 V V_{L4} = 5.1 V (VLCD = 12H)		1.12	3.70	μA
			$V_{DD} = EV_{DD}$ = 3.0 V V_{L4} = 3.0 V (VLCD = 04H)		0.63	2.20	μA
	I_{LCD3} Note 11	Capacitor split method	$V_{DD} = EV_{DD}$ = 3.0 V V_{L4} = 3.0 V		0.12	0.50	μA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, $AV_{REFP} = V_{DD}$ = 3.0 V		1.20	2.04	mA
		CSI/UART operation			0.70	1.54	mA

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

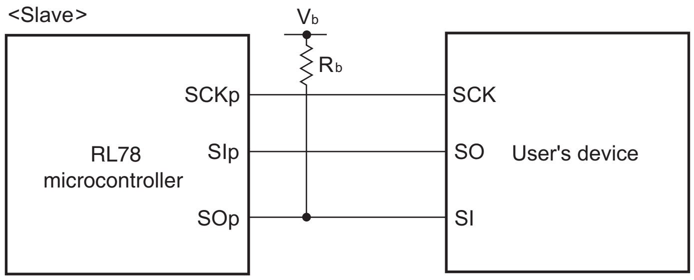
2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SOp) pull-up resistance,
C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),
g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

3.7.2 Internal voltage boosting method

(1) 1/3 bias method

(T_A = –40 to +105°C, 2.4 V $\leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4[Note 1] = 0.47 μF	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V_{L2}	C1 to C4[Note 1] = 0.47 μF		2 V_{L1} –0.1	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L4}	C1 to C4[Note 1] = 0.47 μF		3 V_{L1} –0.15	3 V_{L1}	3 V_{L1}	V
Reference voltage setup time[Note 2]	t_{VWAIT1}			5			ms
Voltage boost wait time[Note 3]	t_{VWAIT2}	C1 to C4[Note 1] = 0.47 μF		500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 µF±30%

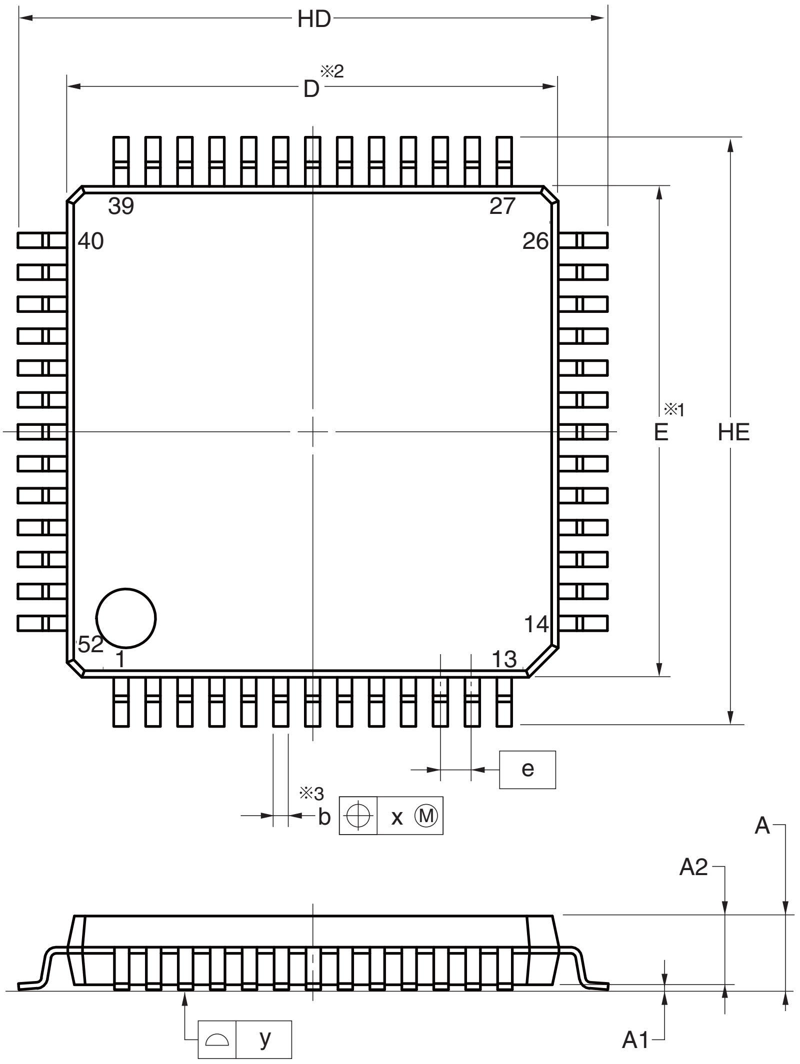
2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected [by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B] if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

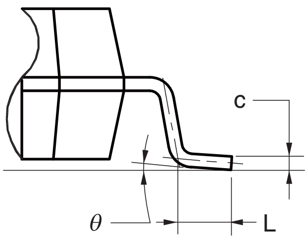
4.4 52-pin Products

R5F10RJ8AFA, R5F10RJAAFA, R5F10RJCAFA
R5F10RJ8GFA, R5F10RJAGFA, R5F10RJCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	10.00±0.10
E	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
A	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32±0.05
c	0.145±0.055
L	0.50±0.15
θ	0° to 8°
e	0.65
x	0.13
y	0.10

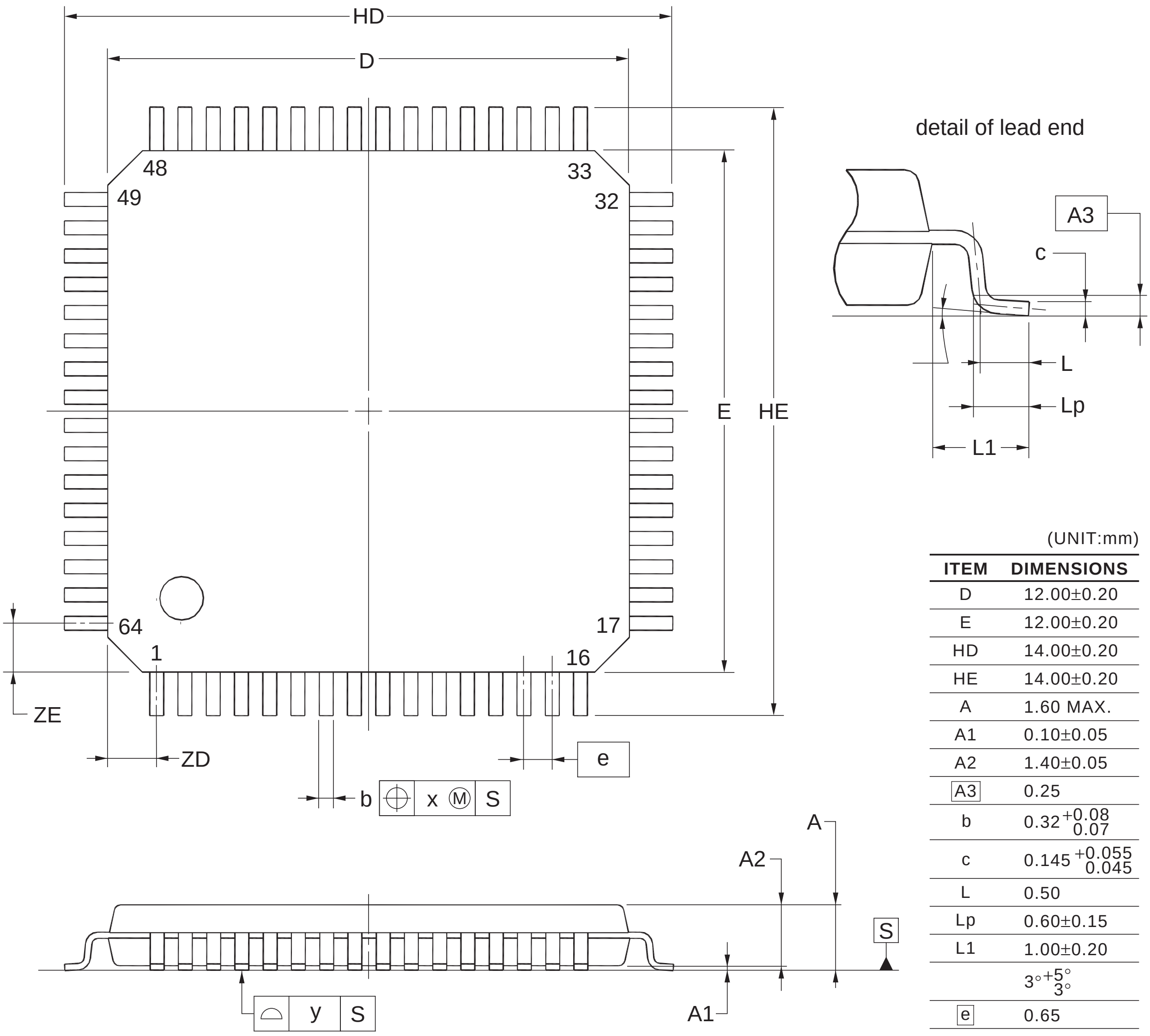
NOTE1.Dimensions “※1” and “※2” do not include mold flash.

2.Dimension “※3” does not include trim offset.

4.5 64-pin Products

R5F10RLAAFA, R5F10RLCAFA
R5F10RLAGFA, R5F10RLCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
$\boxed{A3}$	0.25
b	$0.32^{+0.08}_{0.07}$
c	$0.145^{+0.055}_{0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
	$3^{\circ}{}^{+5^{\circ}}_{3^{\circ}}$
$\boxed{e}$	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

Rev.	Date	Description	
		Page	Summary
2.00	Jan 10, 2014	35	Modification of table in 2.4 AC Characteristics
		36	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		37	Modification of AC Timing Test Points and External System Clock Timing
		39	Modification of AC Timing Test Points
		39	Modification of description, notes 1 and 2 in (1) During communication at same potential (UART mode)
		41, 42	Modification of description, remark 2 in (2) During communication at same potential (CSI mode)
		42, 43	Modification of description in (3) During communication at same potential (CSI mode)
		45	Modification of description, notes 1 and 3, and remark 3 in (4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		46, 48	Modification of description, and remark 3 in (4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		49, 50	Modification of table, and note 1, caution, and remark 3 in (5) Communication at different potential (2.5 V, 3 V) (CSI mode)
		51	Modification of table and note in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (1/3)
		52	Modification of table and notes 1 to 3 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (2/3)
		53, 54	Modification of table, note 3, and remark 3 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (3/3)
		56	Modification of table in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		57	Modification of table in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		59, 60	Addition of (1) I^2C standard mode
		61	Addition of (2) I^2C fast mode
		62	Addition of (3) I^2C fast mode plus
		63	Addition of table in 2.6.1 A/D converter characteristics
		63, 64	Modification of description and notes 3 to 5 in 2.6.1 (1)
		65	Modification of description, notes 3 and 4 in 2.6.1 (2)
		66	Modification of description, notes 3 and 4 in 2.6.1 (3)
		67	Modification of description, notes 3 and 4 in 2.6.1 (4)
		67	Modification of the table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		68	Modification of the table and note in 2.6.3 POR circuit characteristics
		70	Modification of the table of LVD Detection Voltage of Interrupt & Reset Mode
		70	Modification from V_{DD} rise slope to Power supply voltage rising slope in 2.6.5 Supply voltage rise time
		75	Modification of description in 2.10 Dedicated Flash Memory Programmer Communication (UART)
		76	Modification of the figure in 2.11 Timing Specifications for Switching Flash Memory Programming Modes
		77 to 126	Addition of products for industrial applications (G: T_A = -40 to +105°C)
		127 to 133	Addition of product names for industrial applications (G: T_A = -40 to +105°C)
2.10	Sep 30, 2016	5	Modification of pin configuration in 1.3.1 32-pin products
		6	Modification of pin configuration in 1.3.2 44-pin products
		7	Modification of pin configuration in 1.3.3 48-pin products
		8	Modification of pin configuration in 1.3.4 52-pin products
		9, 10	Modification of pin configuration in 1.3.5 64-pin products
		17	Modification of description of main system clock in 1.6 Outline of Functions
		74	Modification of title of 2.8 RAM Data Retention Characteristics, Note, and figure
		74	Modification of table of 2.9 Flash Memory Programming Characteristics
		123	Modification of title of 3.8 RAM Data Retention Characteristics, Note, and figure
		123	Modification of table of 3.9 Flash Memory Programming Characteristics and addition of Note 4
		131	Modification of 4.5 64-pin Products